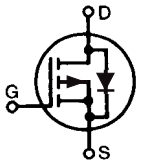
IXYS

TrenchP™ Power MOSFETs

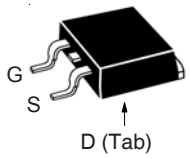
IXTA96P085T
IXTP96P085T
IXTH96P085T

V_{DSS} = - 85V
I_{D25} = - 96A
$R_{DS(on)}$ ≤ 13mΩ

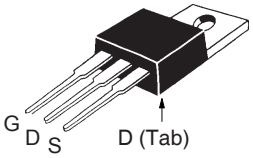
P-Channel Enhancement Mode
Avalanche Rated



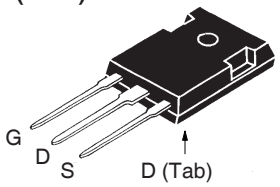
TO-263 AA (IXTA)



TO-220AB (IXTP)



TO-247 (IXTH)



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	- 85	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	- 85	V
V_{GSS}	Continuous	±15	V
V_{GSM}	Transient	±25	V
I_{D25}	T_C = 25°C	- 96	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	- 300	A
I_A	T_C = 25°C	- 48	A
E_{AS}	T_C = 25°C	1	J
P_D	T_C = 25°C	298	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6mm (0.062 in.) from Case for 10s	300	°C
T_{SOLD}	Plastic Body for 10s	260	°C
M_d	Mounting Torque (TO-220 & TO-247)	1.13/10	Nm/lb.in.
Weight	TO-263	2.5	g
	TO-220	3.0	g
	TO-247	6.0	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = - 250μA	- 85			V
$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250μA	- 2.0		- 4.0	V
I_{GSS}	V_{GS} = ± 15V, V_{DS} = 0V			±100	nA
I_{DSS}	V_{DS} = V_{DSS}, V_{GS} = 0V			- 10	μA
	T_J = 125°C			- 750	μA
$R_{DS(on)}$	V_{GS} = -10V, I_D = 0.5 • I_{D25}, Note 1			13	mΩ

Features

- International Standard Packages
- Avalanche Rated
- Extended FBSOA
- Fast Intrinsic Diode
- Low $R_{DS(ON)}$ and Q_G

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- High-Side Switching
- Push Pull Amplifiers
- DC Choppers
- Automatic Test Equipment
- Current Regulators
- Battery Charger Applications

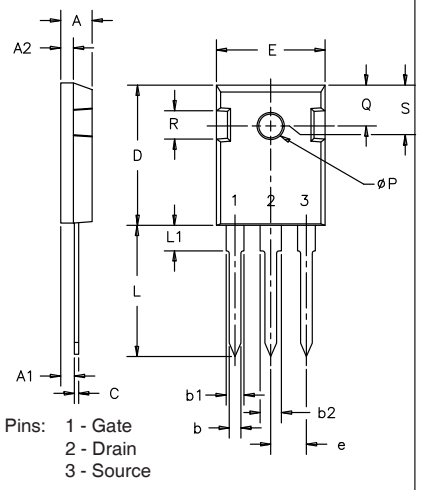
Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = -10V, I_D = 0.5 • I_{D25}, Note 1	40	66		S
C_{iss}	V_{GS} = 0V, V_{DS} = - 25V, f = 1MHz		13.1		nF
C_{oss}			1175		pF
C_{rss}			460		pF
$t_{d(on)}$	**Resistive Switching Times**		23		ns
t_r	V_{GS} = -10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		34		ns
$t_{d(off)}$	R_G = 1Ω (External)		45		ns
t_f			22		ns
$Q_{g(on)}$	V_{GS} = -10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		180		nC
Q_{gs}			52		nC
Q_{gd}			62		nC
R_{thJC}				0.42	°C/W
R_{thCS}	TO-220		0.50		°C/W
	TO-247		0.21		°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			- 96	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			- 394	A
V_{SD}	I_F = - 48A, V_{GS} = 0V, Note 1			-1.3	V
t_{rr}	I_F = - 48A, -di/dt = -100A/μs		55		ns
Q_{RM}	V_R = - 43V, V_{GS} = 0V		100		nC
I_{RM}			- 3.6		A

Note 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

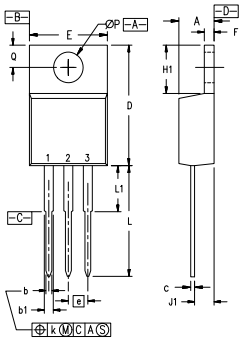
TO-247 Outline



Pins: 1 - Gate
2 - Drain
3 - Source

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.185	.209	4.7	5.3
A_1	.087	.102	2.2	2.54
A_2	.059	.098	2.2	2.6
b	.040	.055	1.0	1.4
b_1	.065	.084	1.65	2.13
b_2	.113	.123	2.87	3.12
C	.016	.031	.4	.8
D	.819	.845	20.80	21.46
E	.610	.640	15.75	16.26
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1		.177		4.50
øP	.140	.144	3.55	3.65
Q	.212	.244	5.4	6.2
R	.170	.216	4.32	5.49
S	.242 BSC		6.15 BSC	

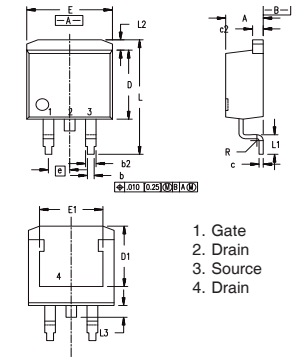
TO-220 Outline



Pins: 1 - Gate 2 - Drain
3 - Source

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
øP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

TO-263 Outline



1. Gate
2. Drain
3. Source
4. Drain

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.06	4.83	.160	.190
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.40	0.74	.016	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	8.00	8.89	.280	.320
E	9.65	10.41	.380	.405
E1	6.22	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.13	0	.005

IXYS Reserves The Right to Change Limits, Test Conditions, and Dimensions.

Fig. 1. Output Characteristics @ T_J = 25ºC

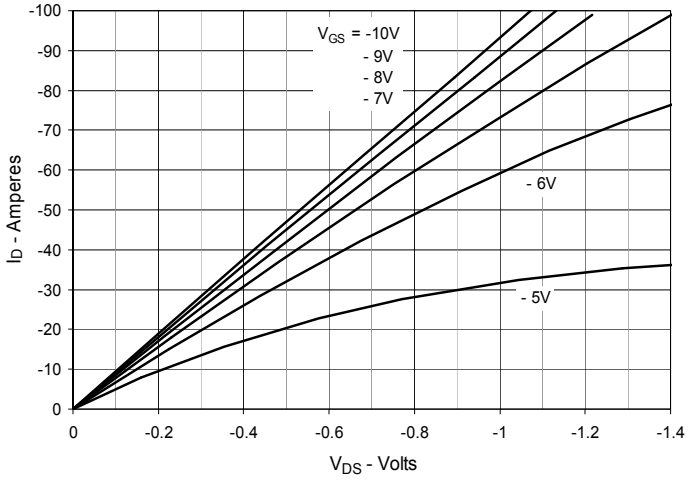


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

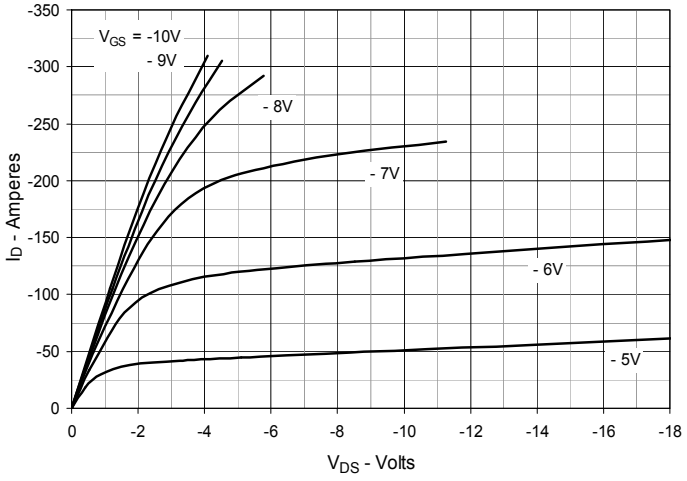


Fig. 3. Output Characteristics @ T_J = 125ºC

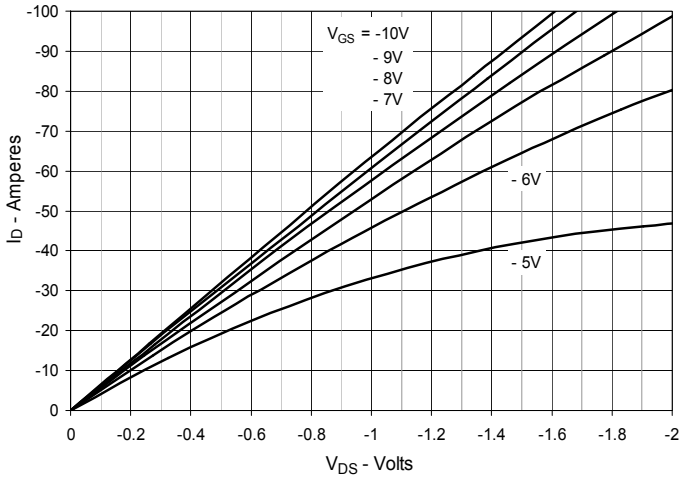


Fig. 4. $R_{DS(on)}$ Normalized to I_D = - 48A Value vs. Junction Temperature

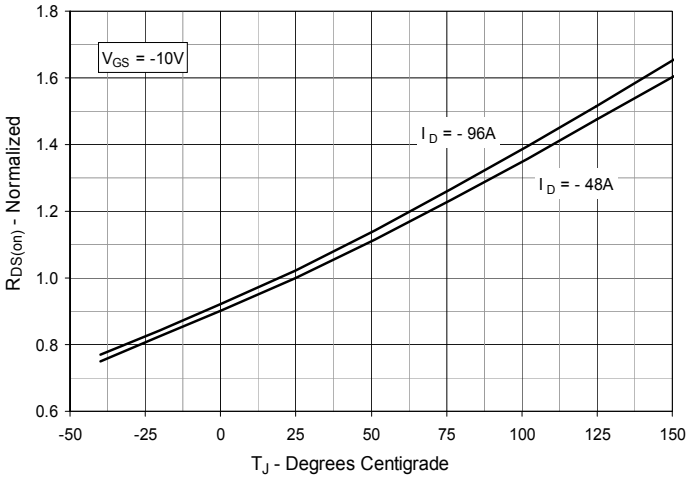


Fig. 5. $R_{DS(on)}$ Normalized to I_D = - 48A Value vs. Drain Current

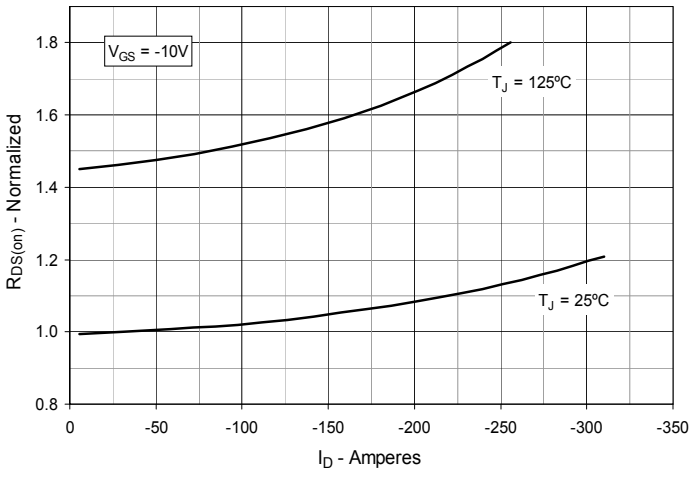


Fig. 6. Maximum Drain Current vs. Case Temperature

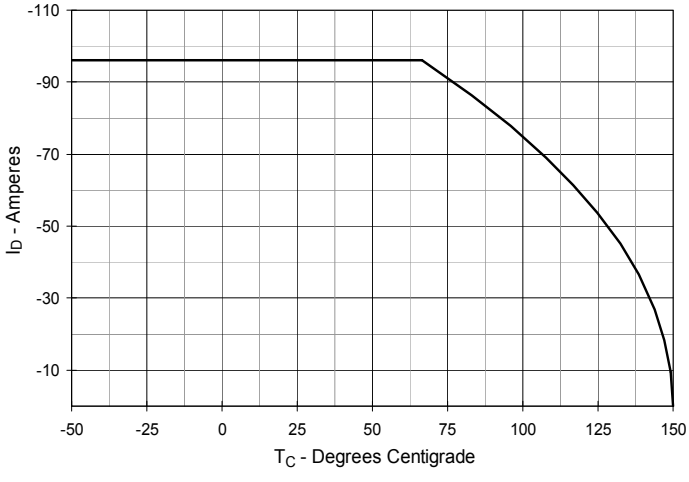


Fig. 7. Input Admittance

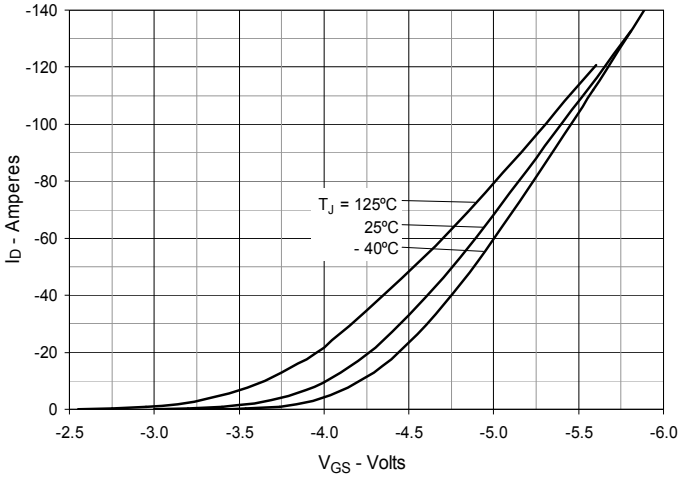


Fig. 8. Transconductance

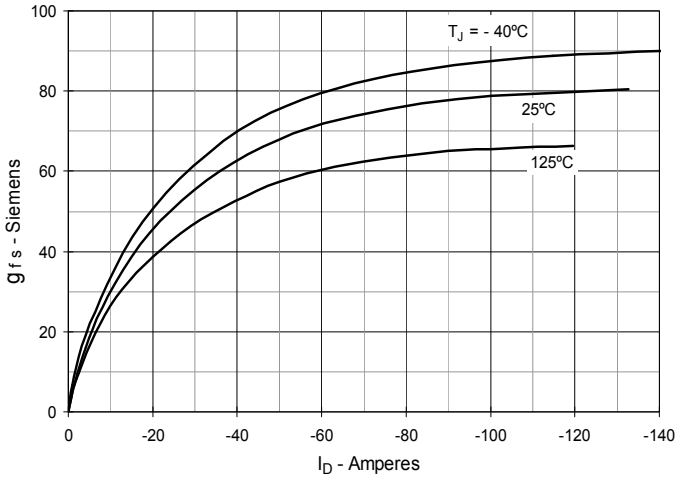


Fig. 9. Forward Voltage Drop of Intrinsic Diode

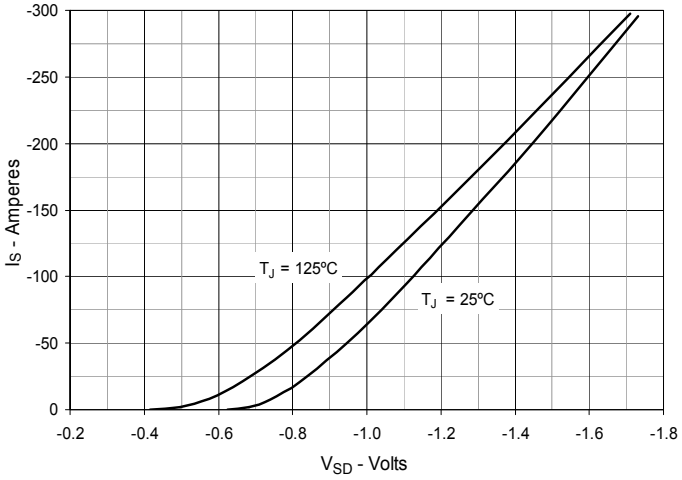


Fig. 10. Gate Charge

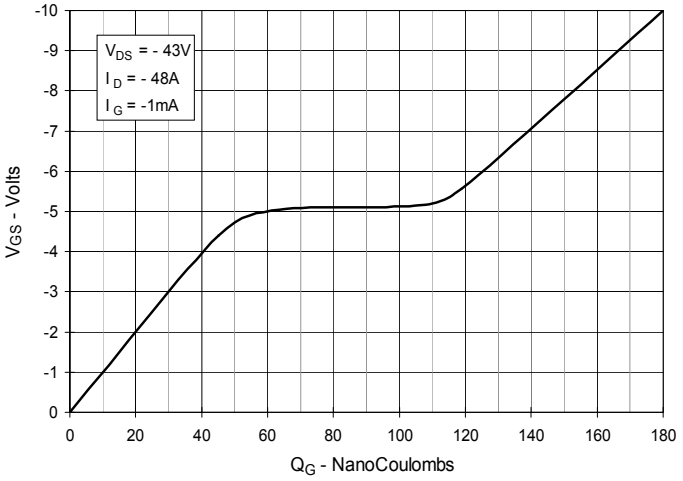


Fig. 11. Capacitance

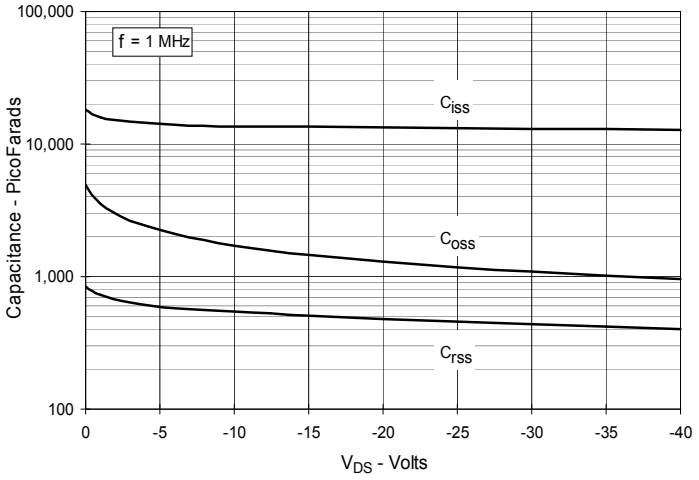


Fig. 12. Forward-Bias Safe Operating Area

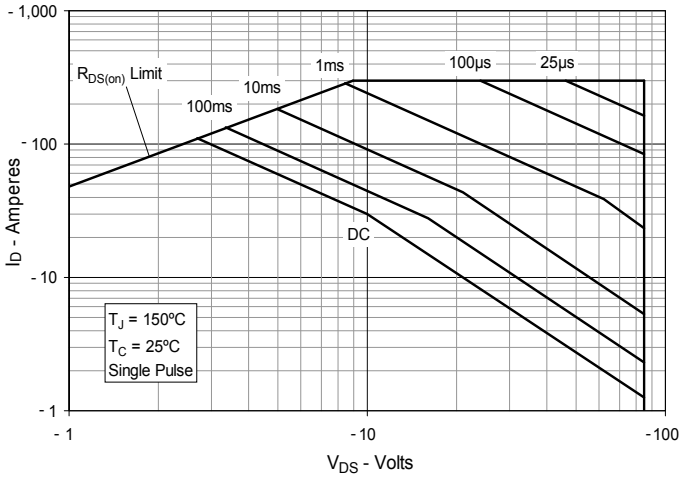


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

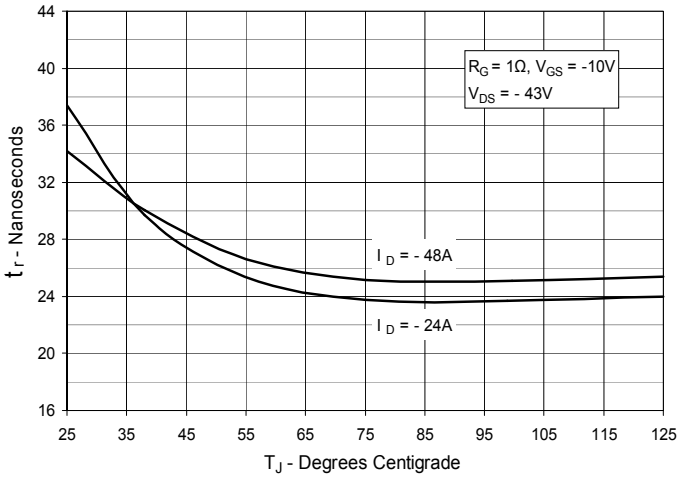


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

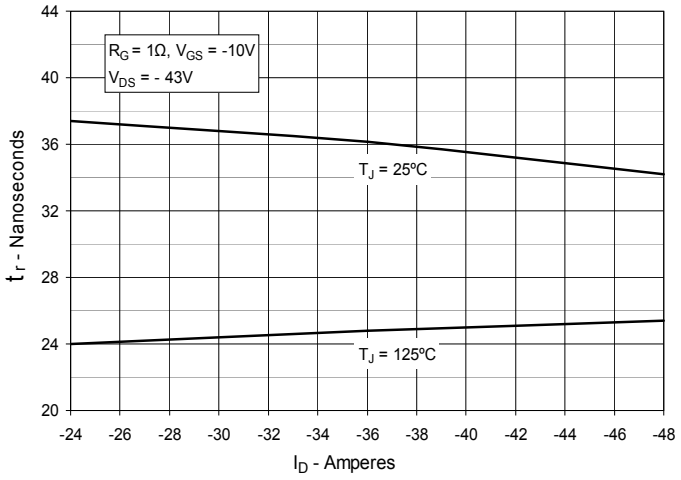


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

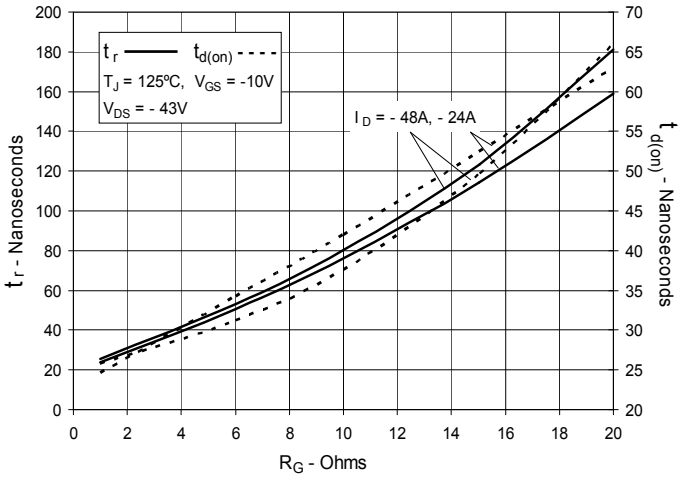


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

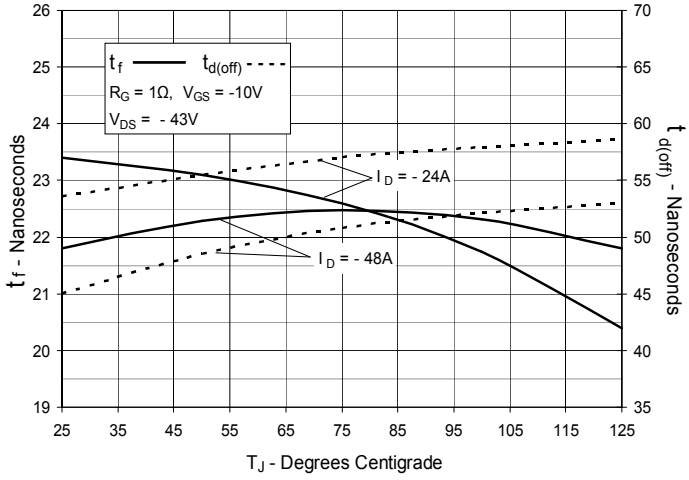


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

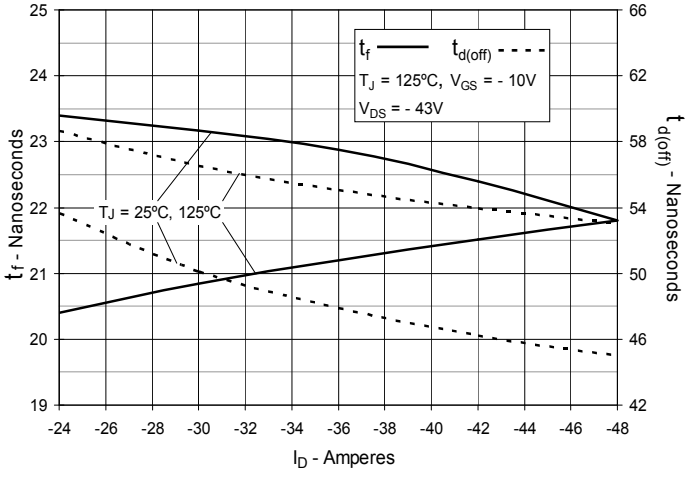


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

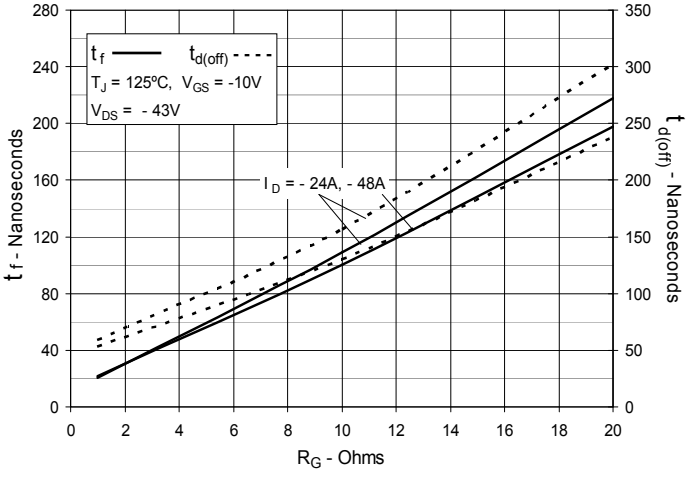


Fig. 19. Maximum Transient Thermal Impedance